NSN 5961-01-367-1967

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-367-1967 **Inclosure Material:** Metal **Overall Length:** Between 0.670 inches and 0.710 inches **Terminal Length:** Between 0.200 inches and 0.225 inches **Overall Height:** Between 0.400 inches and 0.600 inches **Overall Width:** Between 0.175 inches and 0.225 inches **End Application:** B-2 aircraft **Mounting Method: Terminal Features Provided:** Gold plated leads **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, dc and 0.98 forward voltage, dc **Current Rating Per Characteristic:** 100.00 nanoamperes forward current, average peak **Special Features:** Hardness critical process; junction pattern arrangement: pn **Nuclear Hardness Critical Feature:** Hardened **Precious Material And Location:** Terminals gold **Precious Material:** Gold **Terminal Type And Quantity:** 2 tab, solder lug Shelf Life: N/a **Unit Of Measure: Demilitarization:**

Yes - demil/mli

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